



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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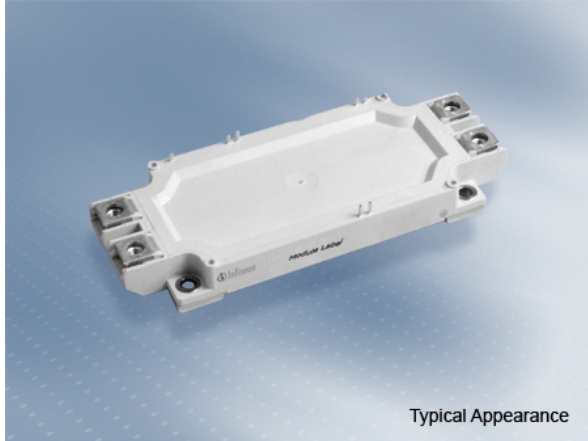
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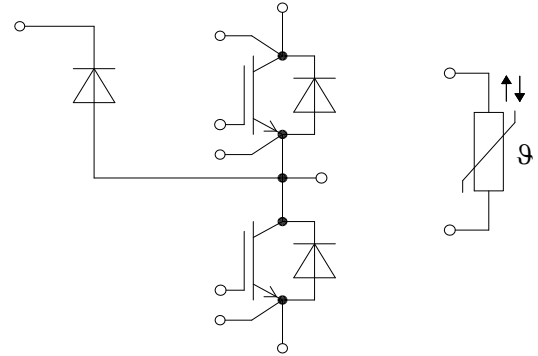
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EconoDUAL™3 Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled Diode und NTC
EconoDUAL™3 module with trench/fieldstop IGBT4 and Emitter Controlled Diode and NTC



Typical Appearance



$V_{CES} = 650V$
 $I_{C\ nom} = 400A / I_{CRM} = 800A$

Typische Anwendungen

- 3-Level-Applikationen

Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur $T_{vj\ op}$
- Niedrige Schaltverluste
- Niedriges V_{CEsat}
- Sehr große Robustheit
- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} mit positivem Temperaturkoeffizienten

Mechanische Eigenschaften

- Isolierte Bodenplatte
- Standardgehäuse

Typical Applications

- 3-Level-Applications

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Low Switching Losses
- Low V_{CEsat}
- Unbeatable Robustness
- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} with positive Temperature Coefficient

Mechanical Features

- Isolated Base Plate
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

| Content of the Code | Digit |
|----------------------------|---------|
| Module Serial Number | 1 - 5 |
| Module Material Number | 6 - 11 |
| Production Order Number | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

| | | |
|-----------------|---------------------------------|----------------------|
| prepared by: MK | date of publication: 2013-11-11 | |
| approved by: MK | revision: 3.1 | UL approved (E83335) |



IGBT, Wechselrichter / IGBT, Inverter
Höchstzulässige Werte / Maximum Rated Values

| | | | | |
|--|--|----------------------------|------------|--------|
| Kollektor-Emitter-Sperrspannung Collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 650 | V |
| Kollektor-Dauergleichstrom Continuous DC collector current | $T_C = 50^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$ I_C | 400 450 | A A |
| Periodischer Kollektor-Spitzenstrom Repetitive peak collector current | $t_P = 1\text{ ms}$ | I_{CRM} | 800 | A |
| Gesamt-Verlustleistung Total power dissipation | $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | P_{tot} | 1150 | W |
| Gate-Emitter-Spitzenspannung Gate-emitter peak voltage | | V_{GES} | +/-20 | V |

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | | |
|---|---|---|--------------------|-------------------------|------|-------------|---|
| Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage | $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,55 1,70 1,75 | 1,95 | V V V | |
| Gate-Schwellenspannung Gate threshold voltage | $I_C = 6,40\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | | V_{GEth} | 4,9 | 5,8 | 6,5 | V |
| Gateladung Gate charge | $V_{GE} = -15\text{ V} \dots +15\text{ V}$ | | Q_G | 4,30 | | | μC |
| Interner Gatewiderstand Internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | | R_{Gint} | 1,0 | | | Ω |
| Eingangskapazität Input capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{ies} | 26,0 | | | nF |
| Rückwirkungskapazität Reverse transfer capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{res} | 0,76 | | | nF |
| Kollektor-Emitter-Reststrom Collector-emitter cut-off current | $V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{CES} | | | 1,0 | mA |
| Gate-Emitter-Reststrom Gate-emitter leakage current | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{GES} | | | 100 | nA |
| Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{don} | 0,12 0,12 0,12 | | | μs μs μs |
| Anstiegszeit, induktive Last Rise time, inductive load | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_r | 0,14 0,14 0,14 | | | μs μs μs |
| Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{doff} | 0,63 0,66 0,67 | | | μs μs μs |
| Fallzeit, induktive Last Fall time, inductive load | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_f | 0,065 0,075 0,088 | | | μs μs μs |
| Einschaltverlustenergie pro Puls Turn-on energy loss per pulse | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2550\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{on} | 13,5 17,0 17,5 | | | mJ mJ mJ |
| Abschaltverlustenergie pro Puls Turn-off energy loss per pulse | $I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 3,6\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{off} | 21,0 25,0 26,0 | | | mJ mJ mJ |
| Kurzschlußverhalten SC data | $V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ | $t_P \leq 10\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ | I_{SC} | 1900 1500 | | | A A |
| Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case | pro IGBT / per IGBT | | R_{thJC} | | | 0,13 | K/W |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | | | 0,027 | K/W |
| Temperatur im Schaltbetrieb Temperature under switching conditions | | | $T_{vj\text{op}}$ | -40 | | 150 | $^{\circ}\text{C}$ |

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Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

| | | | | |
|---|--|-----------|----------------|--|
| Periodische Spitzensperrspannung Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 650 | V |
| Dauergleichstrom Continuous DC forward current | | I_F | 400 | A |
| Periodischer Spitzenstrom Repetitive peak forward current | $t_P = 1\text{ ms}$ | I_{FRM} | 800 | A |
| Grenzlastintegral I^2t - value | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 11000 10000 | A^2s A^2s |

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|---|--|---|--------------------|----------------------|-------|---|
| Durchlassspannung Forward voltage | $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,55 1,50 1,45 | 1,95 | V V V |
| Rückstromspitze Peak reverse recovery current | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 115 165 185 | | A A A |
| Sperrverzögerungsladung Recovered charge | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 23,0 34,0 42,0 | | μC μC μC |
| Abschaltenergie pro Puls Reverse recovery energy | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 3,80 6,30 8,00 | | mJ mJ mJ |
| Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case | pro Diode / per diode | | R_{thJC} | | 0,25 | K/W |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | | 0,053 | K/W |
| Temperatur im Schaltbetrieb Temperature under switching conditions | | | $T_{vj\text{ op}}$ | -40 | 150 | $^{\circ}\text{C}$ |

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Diode, 3-Level / Diode, 3-Level

Höchstzulässige Werte / Maximum Rated Values

| | | | | |
|---|--|-----------|----------------|--|
| Periodische Spitzensperrspannung Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 650 | V |
| Dauergleichstrom Continuous DC forward current | | I_F | 400 | A |
| Periodischer Spitzenstrom Repetitive peak forward current | $t_P = 1\text{ ms}$ | I_{FRM} | 800 | A |
| Grenzlastintegral I^2t - value | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 11000 10000 | A^2s A^2s |

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|---|---|---|--------------------|----------------------|-------|---|
| Durchlassspannung Forward voltage | $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,55 1,50 1,45 | 1,95 | V V V |
| Rückstromspitze Peak reverse recovery current | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 115 165 185 | | A A A |
| Sperrverzögerungsladung Recovered charge | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 23,0 34,0 42,0 | | μC μC μC |
| Abschaltenergie pro Puls Reverse recovery energy | $I_F = 400\text{ A}, -di_F/dt = 2550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 3,80 6,30 8,00 | | mJ mJ mJ |
| Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case | pro Diode / per diode | | R_{thJC} | | 0,25 | K/W |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | | 0,053 | K/W |
| Temperatur im Schaltbetrieb Temperature under switching conditions | | | $T_{vj\text{ op}}$ | -40 | 150 | $^{\circ}\text{C}$ |

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|--|--------------|------|------|------------------|
| Nennwiderstand Rated resistance | $T_C = 25^{\circ}\text{C}$ | | R_{25} | 5,00 | | $\text{k}\Omega$ |
| Abweichung von R100 Deviation of R100 | $T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$ | | $\Delta R/R$ | -5 | 5 | % |
| Verlustleistung Power dissipation | $T_C = 25^{\circ}\text{C}$ | | P_{25} | | 20,0 | mW |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/50}$ | 3375 | | K |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/80}$ | 3411 | | K |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/100}$ | 3433 | | K |

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

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Modul / Module

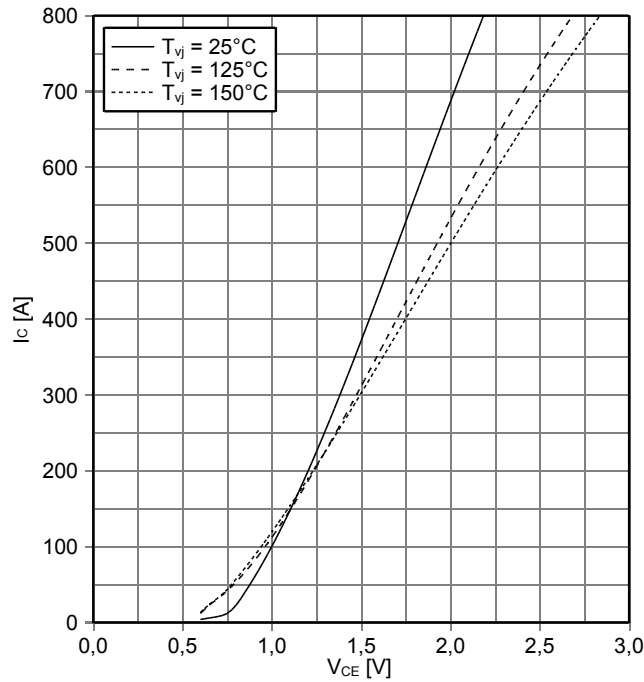
| | | | | | |
|--|--|---------------------|--------------------------------|-----|---------|
| Isolations-Prüfspannung Isolation test voltage | RMS, f = 50 Hz, t = 1 min | V _{ISOL} | 2,5 | | kV |
| Material Modulgrundplatte Material of module baseplate | | | Cu | | |
| Innere Isolation Internal isolation | Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140) | | Al ₂ O ₃ | | |
| Kriechstrecke Creepage distance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 14,5 13,0 | | mm |
| Luftstrecke Clearance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 12,5 10,0 | | mm |
| Vergleichszahl der Kriechwegbildung Comperative tracking index | | CTI | > 200 | | |
| | | | min. typ. max. | | |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$ | R _{thCH} | 0,009 | | K/W |
| Modulstreuintduktivität Stray inductance module | | L _{sCE} | 35 | | nH |
| Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip | T _c = 25°C, pro Schalter / per switch | R _{CC+EE'} | 1,45 | | mΩ |
| Lagertemperatur Storage temperature | | T _{stg} | -40 | 125 | °C |
| Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting | Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note | M | 3,00 | - | 6,00 Nm |
| Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque | Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note | M | 3,0 | - | 6,0 Nm |
| Gewicht Weight | | G | 345 | | g |

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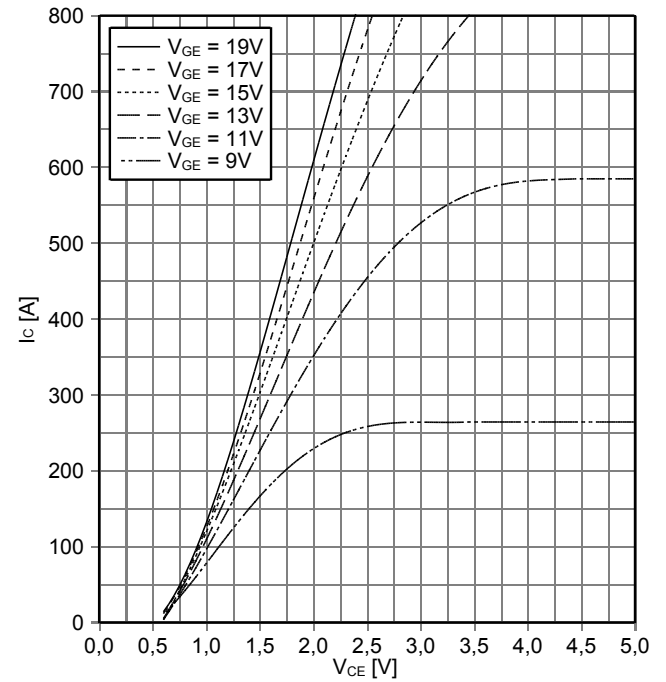
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



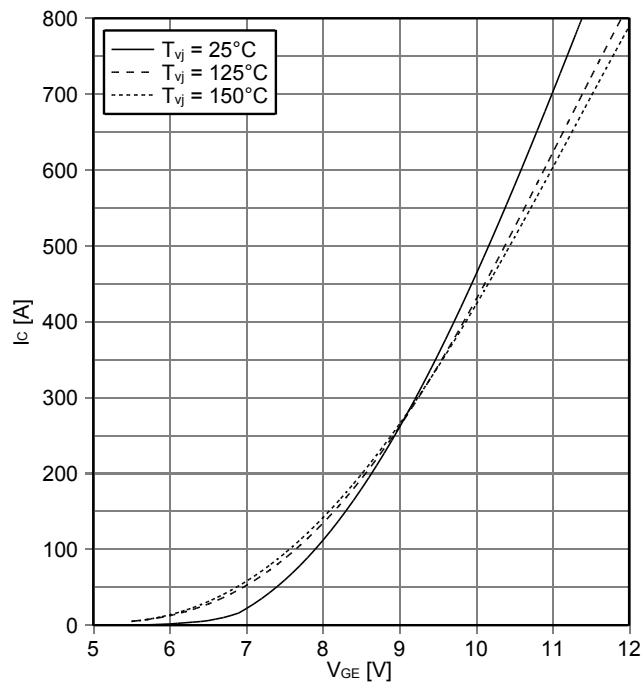
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



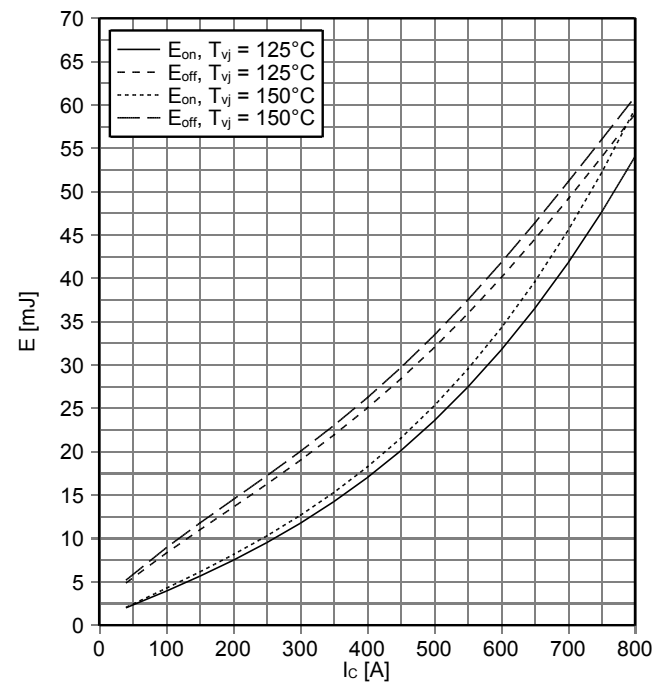
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3.6\ \Omega, R_{Goff} = 3.6\ \Omega, V_{CE} = 300\text{ V}$

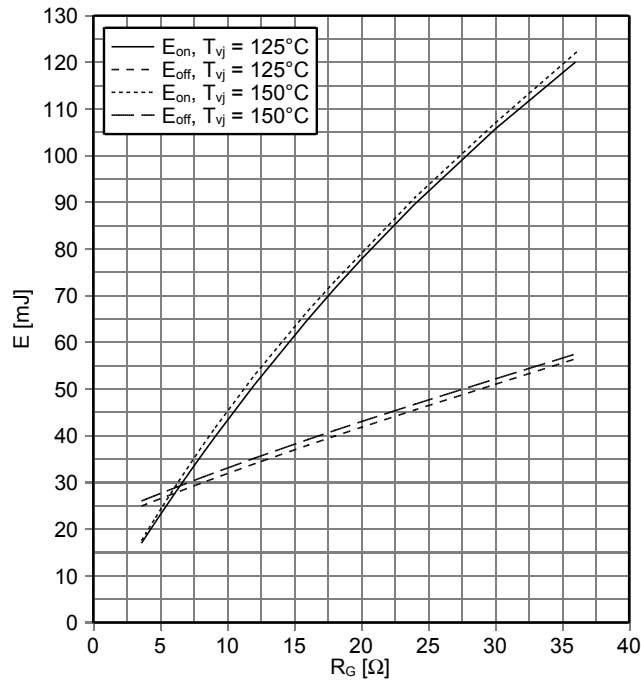


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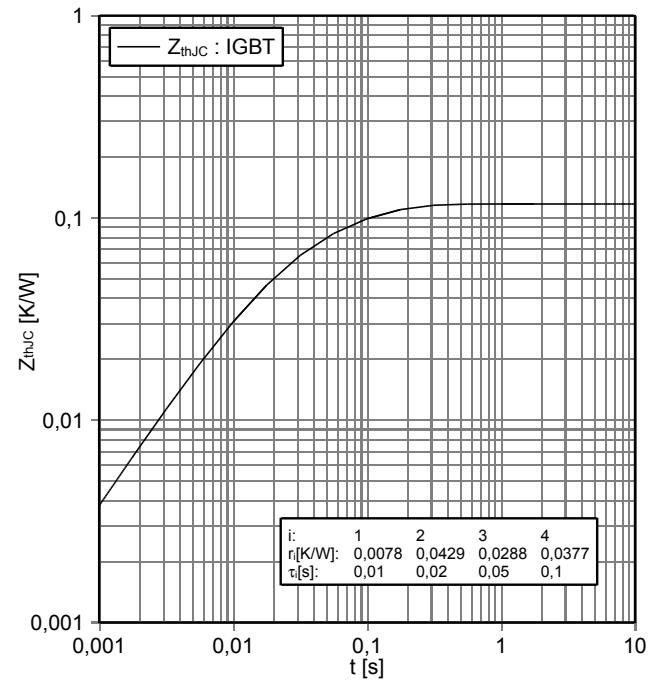
Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 400\text{ A}, V_{CE} = 300\text{ V}$



Transienter Wärmewiderstand IGBT, Wechselrichter
transient thermal impedance IGBT, Inverter

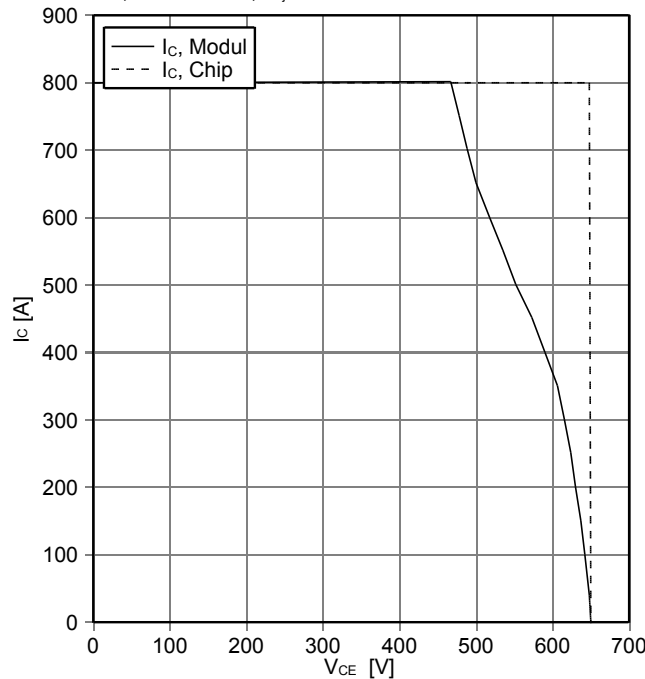
$Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter
(RBSOA)

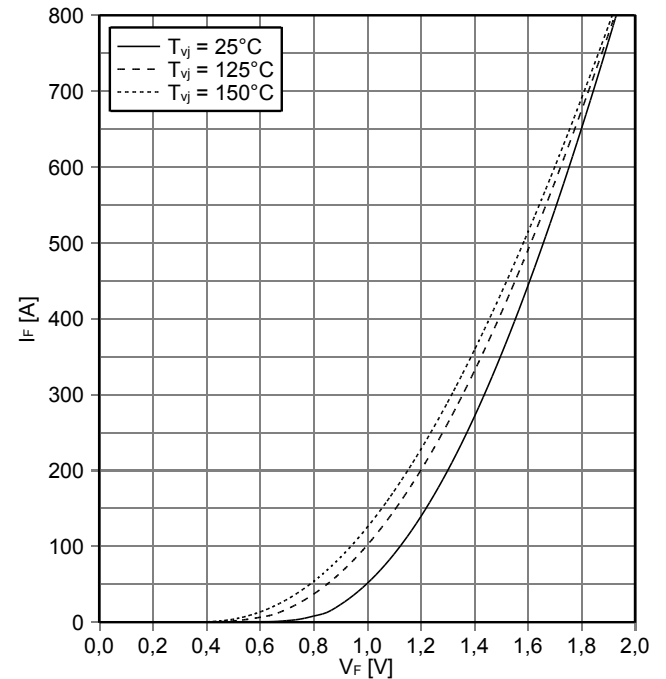
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3.6\ \Omega, T_{vj} = 150^\circ\text{C}$



Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$

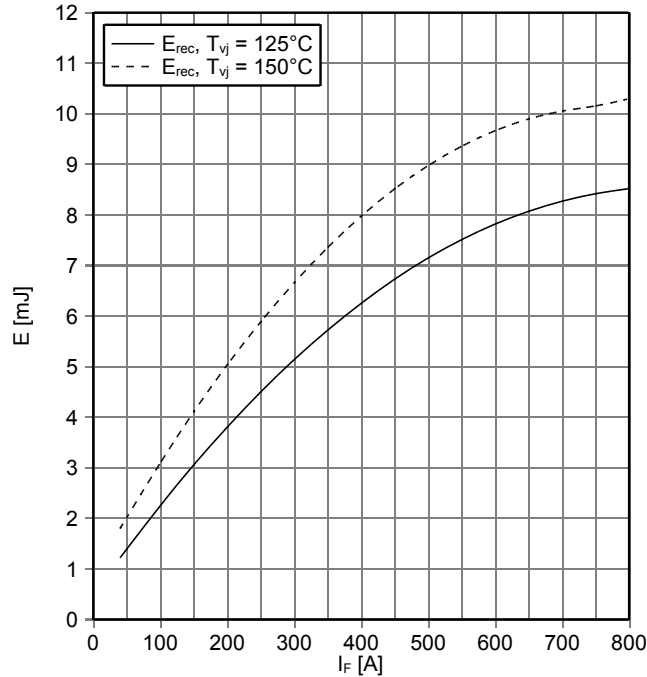


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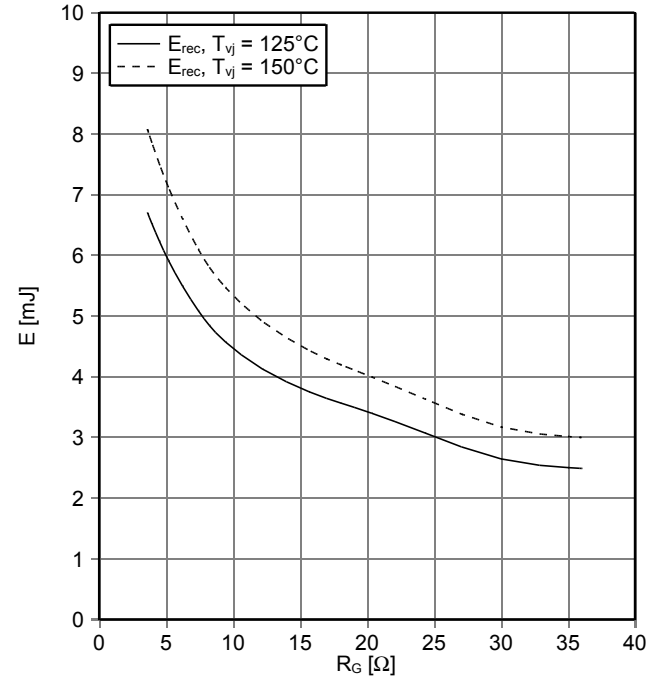
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 3.6 \Omega, V_{CE} = 300 V$



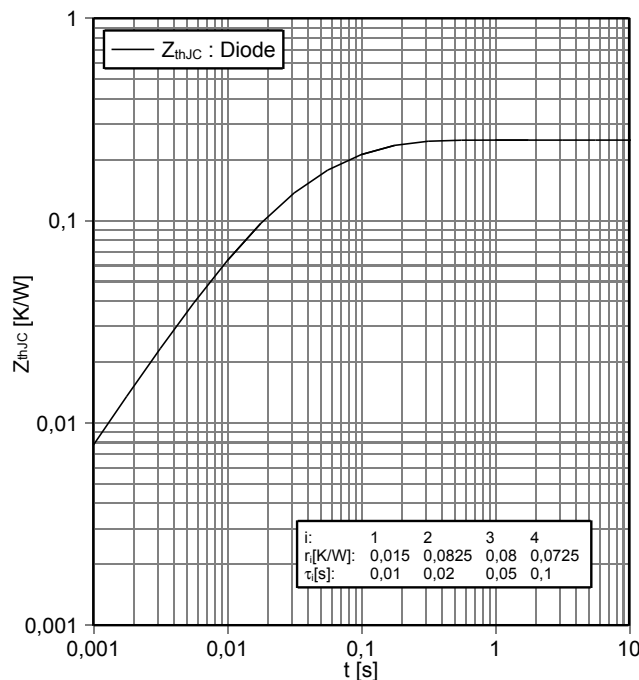
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 400 A, V_{CE} = 300 V$



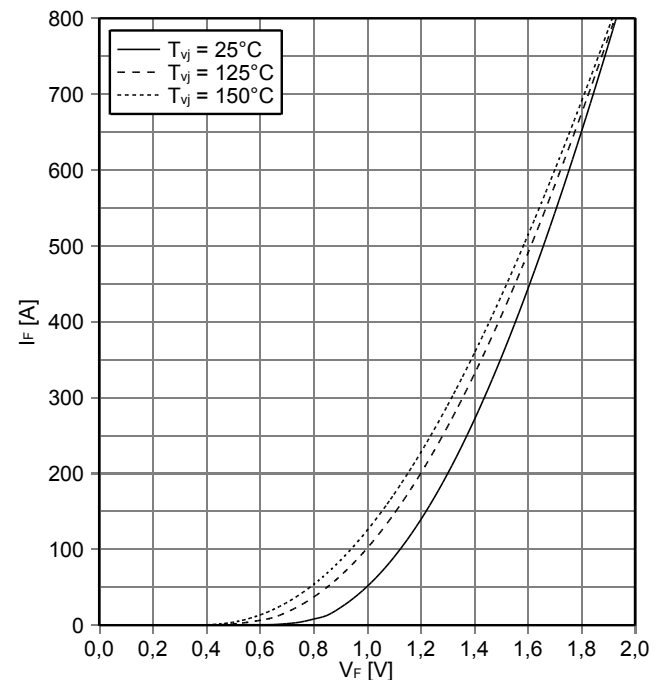
Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



Durchlasskennlinie der Diode, 3-Level (typisch)
forward characteristic of Diode, 3-Level (typical)

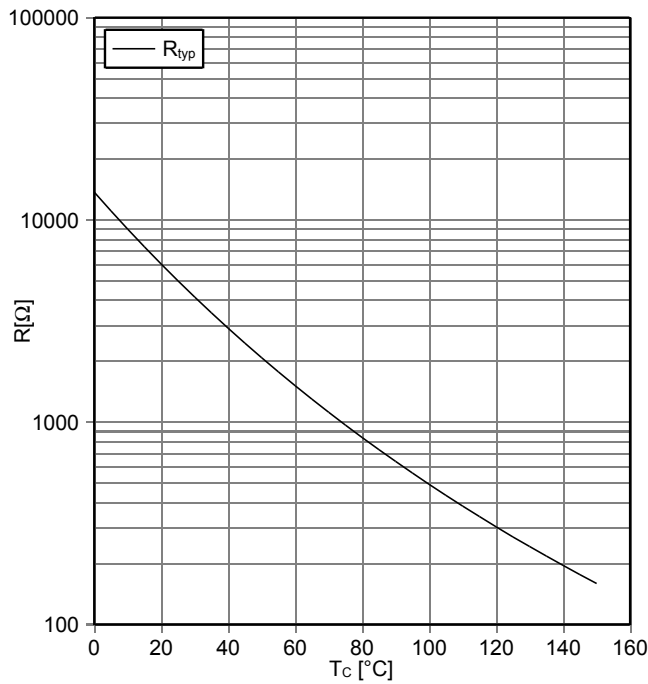
$I_F = f(V_F)$



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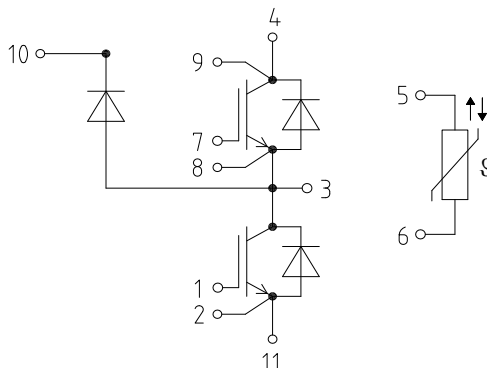


NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$

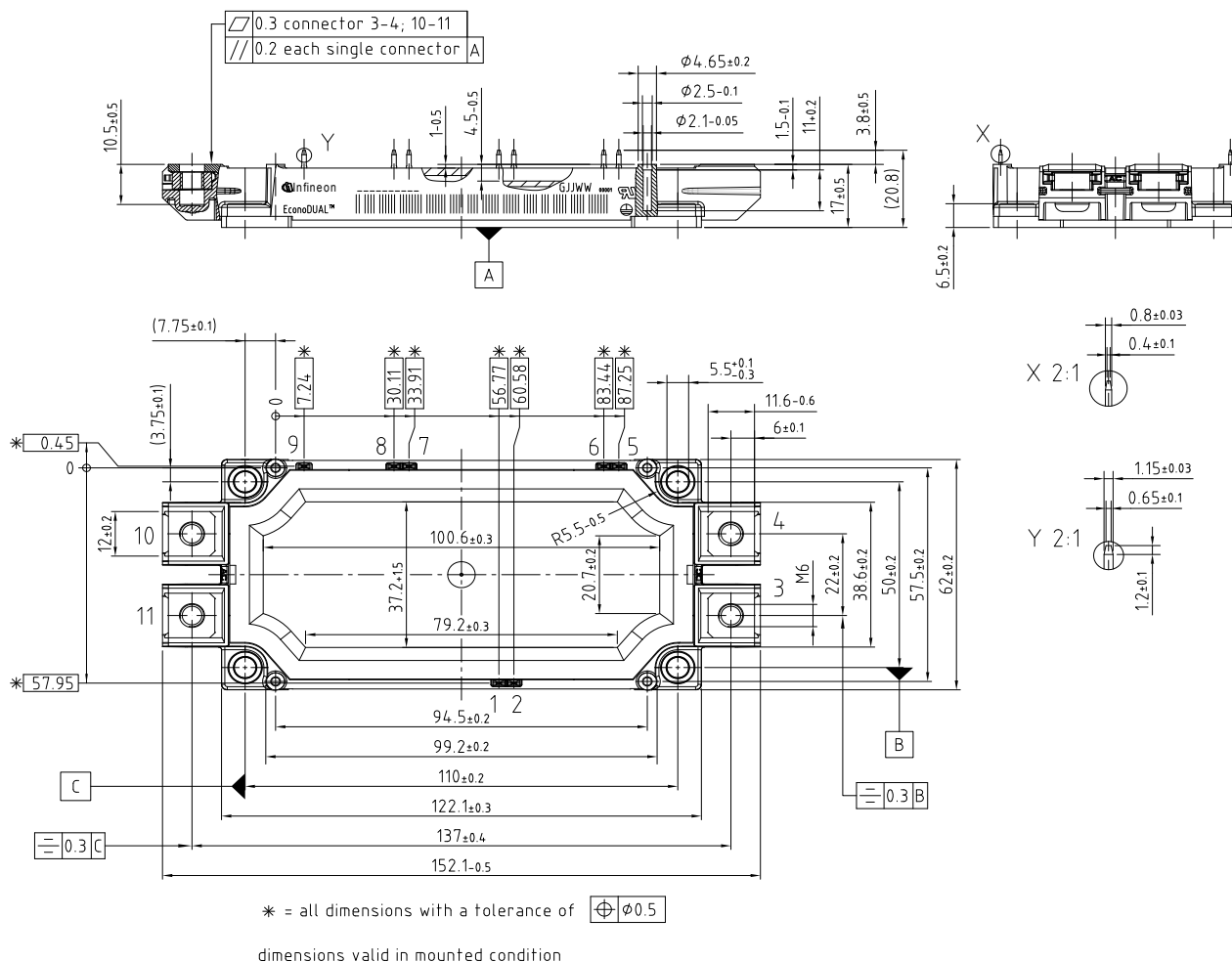


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Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



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